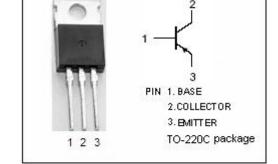


## **isc Silicon PNP Power Transistor**

# MJE15033

### **DESCRIPTION**

- · Collector-Emitter Sustaining Voltage-
  - : V<sub>CEO(SUS)</sub>= -250V(Min)
- · DC current gain -
- :  $h_{FE} = 50 \text{ (Min) } @I_{C} = -0.5 \text{ A}$
- :  $h_{FE} = 10 \text{ (Min) } @I_{C} = -2.0 \text{ A}$
- Complement to Type MJE15032
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



### **APPLICATIONS**

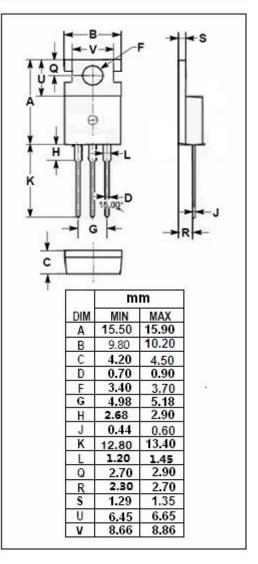
 Designed for use as high–frequency drivers in audio amplifiers.

## ABSOLUTE MAXIMUM RATINGS (Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT	
V <sub>CBO</sub>	Collector-Base Voltage	-250	V	
V <sub>CEO</sub>	Collector-Emitter Voltage	-250	V	
V <sub>EBO</sub>	Emitter-Base Voltage	-5	V	
Ic	Collector Current -Continuous	-8	А	
Ісм	Collector Current-Peak	-16	А	
I <sub>B</sub>	Base Current	-2	А	
Pc	Collector Power Dissipation @T <sub>a</sub> =25°C	2	W	
	Collector Power Dissipation @T <sub>C</sub> =25℃	50		
T <sub>j</sub>	Junction Temperature	150	$^{\circ}$	
T <sub>stg</sub>	Storage Temperature	-65~150	$^{\circ}$	

## THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R <sub>th j-c</sub>	Thermal Resistance, Junction to Case	2.5	°C/W
R <sub>th j-a</sub>	Thermal Resistance, Junction to Ambient	62.5	°C/W





## **isc Silicon PNP Power Transistor**

MJE15033

#### **ELECTRICAL CHARACTERISTICS**

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V <sub>CEO(SUS)</sub>	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = -10mA ;I <sub>B</sub> = 0	-250		V
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	I <sub>C</sub> = -1A ;I <sub>B</sub> = -0.1A		-0.5	V
V <sub>BE(on)</sub>	Base-Emitter On Voltage	I <sub>C</sub> = -1A ; V <sub>CE</sub> = -5V		-1.0	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = -150V; I <sub>E</sub> = 0		-10	μА
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = -5V; I <sub>C</sub> = 0		-10	μА
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = -0.5A ; V <sub>CE</sub> = -5V	50		
h <sub>FE-2</sub>	DC Current Gain	Ic= -1A; VcE= -5V	50		
h <sub>FE-3</sub>	DC Current Gain	I <sub>C</sub> = -2A ; V <sub>CE</sub> = -5V	10		
f⊤	Current Gain-Bandwidth Product	I <sub>C</sub> = -0.5A; V <sub>CE</sub> = -10V; f <sub>test</sub> = 1.0MHz	20		MHz

## **NOTICE:**

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